MOSFET - N-Channel, Small Signal, SOT-23 60 V, 115 mA

2N7002L, 2V7002L

Features

- 2V Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable (2V7002L)
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 $M\Omega$)	V_{DGR}	60	Vdc
Drain Current - Continuous $T_C = 25^{\circ}C$ (Note 1) $T_C = 100^{\circ}C$ (Note 1) - Pulsed (Note 2)	I _D I _D I _{DM}	±115 ±75 ±800	mAdc
Gate-Source Voltage - Continuous - Non-repetitive (t _p ≤ 50 μs)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 3) T _A = 25°C Derate above 25°C Thermal Resistance, Junction-to-Ambient	P_D	225 1.8 556	mW mW/°C °C/W
Total Device Dissipation (Note 4) Alumina Substrate, T _A = 25°C Derate above 25°C Thermal Resistance, Junction-to-Ambient	P _D	300 2.4 417	mW mW/°C °C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- The Power Dissipation of the package may result in a lower continuous drain current.
- 2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.
- 3. FR-5 = 1.0 x 0.75 x 0.062 in.
- 4. Alumina = 0.4 x 0.3 x 0.025 in 99.5% alumina.

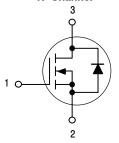


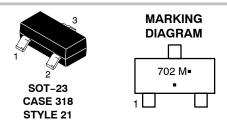
ON Semiconductor®

www.onsemi.com

V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
60 V	7.5 Ω @ 10 V, 500 mA	115 mA

N-Channel





702 = Device Code

M = Date Code*

■ Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or position may
vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
2N7002LT1G		3,000 Tape & Reel
2N7002LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel
2N7002LT7G]`	3,500 Tape & Reel
2V7002LT1G		3,000 Tape & Reel
2V7002LT3G	SOT-23	10,000 Tape & Reel
2N7002LT1H*	(Pb-Free)	3,000 Tape & Reel
2N7002LT7H*		3,500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1

^{*}Not for new design.

2N7002L, 2V7002L

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	•
Drain-Source Breakdown Voltage $(V_{GS} = 0, I_D = 10 \mu Adc)$	V _{(BR)DSS}	60	_	-	Vdc
Zero Gate Voltage Drain Current $T_J = 25^{\circ}C$ $(V_{GS} = 0, V_{DS} = 60 \text{ Vdc})$ $T_J = 125^{\circ}C$	I _{DSS}	- -	- -	1.0 500	μAdc
Gate-Body Leakage Current, Forward (V _{GS} = 20 Vdc)	I _{GSSF}	-	-	100	nAdc
Gate-Body Leakage Current, Reverse (V _{GS} = -20 Vdc)	I _{GSSR}	-	-	-100	nAdc
ON CHARACTERISTICS (Note 5)			•		
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 250 \mu Adc)$	V _{GS(th)}	1.0	_	2.5	Vdc
On–State Drain Current $(V_{DS} \ge 2.0 \ V_{DS(on)}, \ V_{GS} = 10 \ Vdc)$	I _{D(on)}	500	-	-	mA
Static Drain-Source On-State Voltage $(V_{GS} = 10 \text{ Vdc}, I_D = 500 \text{ mAdc})$ $(V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mAdc})$	V _{DS(on)}	- -	- -	3.75 0.375	Vdc
$ \begin{array}{lll} \text{Static Drain-Source On-State Resistance} & & & & \\ \text{(V}_{GS} = 10 \text{ V, I}_D = 500 \text{ mAdc)} & & & & \\ \text{T}_C = 25^{\circ}\text{C} & & & \\ \text{T}_C = 125^{\circ}\text{C} & & \\ \text{(V}_{GS} = 5.0 \text{ Vdc, I}_D = 50 \text{ mAdc)} & & & \\ \text{T}_C = 25^{\circ}\text{C} & & \\ \end{array} $	r _{DS(on)}	- - -	- - -	7.5 13.5 7.5	Ohms
$T_C = 125$ °C		-	-	13.5	
Forward Transconductance ($V_{DS} \ge 2.0 \ V_{DS(on)}$, $I_D = 200 \ mAdc$)	g _{FS}	80	_	-	mS
DYNAMIC CHARACTERISTICS					
Input Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz)	C _{iss}	-	-	50	pF
Output Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz)	C _{oss}	-	_	25	pF
Reverse Transfer Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz)	C _{rss}	-	_	5.0	pF
SWITCHING CHARACTERISTICS (Note 5)					
Turn–On Delay Time $(V_{DD} = 25 \text{ Vdc}, I_D \cong 500 \text{ mAdc},$	t _{d(on)}	-	-	20	ns
Turn–Off Delay Time $R_G = 25 \Omega$, $R_L = 50 \Omega$, $V_{gen} = 10 V$)	t _{d(off)}	-	-	40	ns
BODY-DRAIN DIODE RATINGS					
Diode Forward On-Voltage (I _S = 115 mAdc, V _{GS} = 0 V)	V_{SD}	-	_	-1.5	Vdc
Source Current Continuous (Body Diode)	I _S	-	_	-115	mAdc
Source Current Pulsed	I _{SM}	-	-	-800	mAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

2N7002L, 2V7002L

TYPICAL ELECTRICAL CHARACTERISTICS

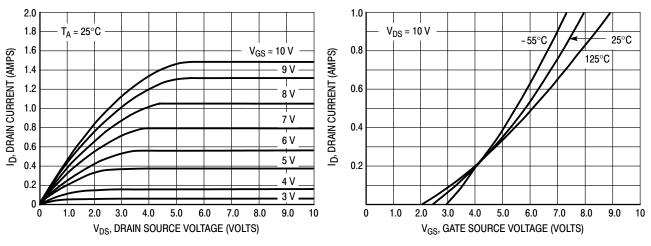


Figure 1. Ohmic Region

Figure 2. Transfer Characteristics

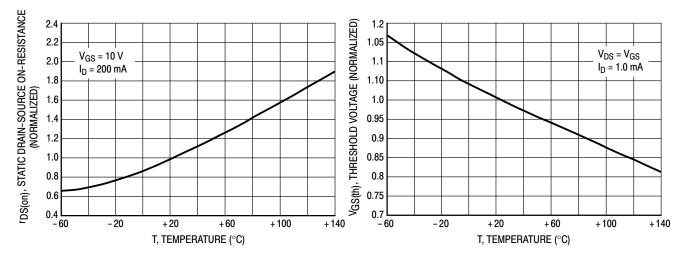


Figure 3. Temperature versus Static Drain-Source On-Resistance

Figure 4. Temperature versus Gate Threshold Voltage



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

PROT	RUSIONS, OR GATE BURRS.	
		T

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	3. GATE	CATHODE-ANODE	ANODE	3. GATE	ANODE

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
CATHODE	CATHODE	ANODE	CATHODE	ANODE	ANODE
ANODE	CATHODE	CATHODE	ANODE	CATHODE-ANOD	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	NO CONNECTION

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
DOCUMENT N	UMBER: 98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

DESCRIPTION:

PAGE 1 OF 1

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative